

Supporting information

Magnetoresistance Effect in Rubrene-based Spin Valves at Room Temperature

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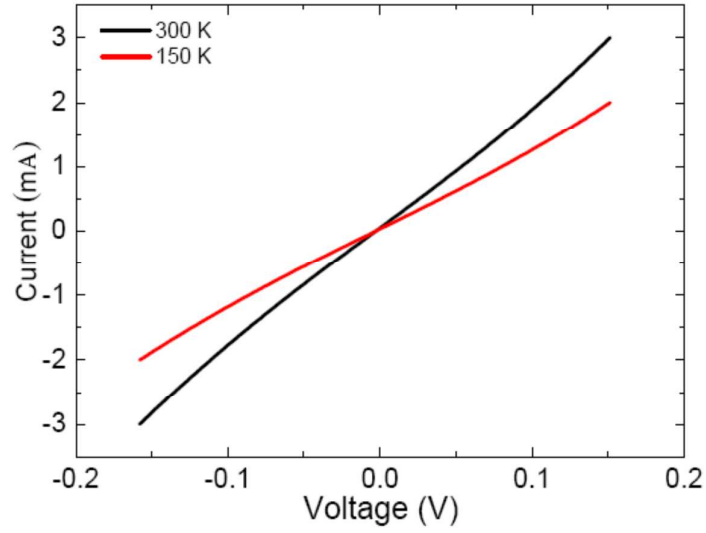


Fig.S1. Nonlinear current–voltage curves for spin valves with 2-nm-thick rubrene layers measured at 300 K and 150 K.

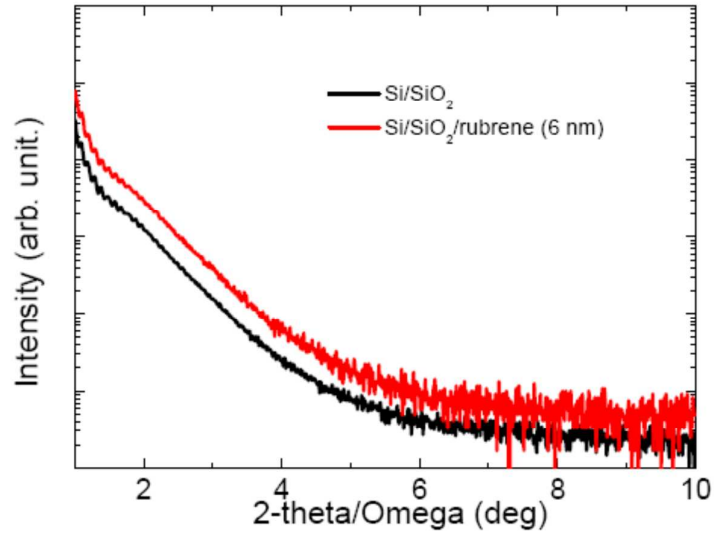


Fig.S2. Grazing angle XRD results.

As shown in Fig. S2, there is no extra peak after rubrene layer deposited on the Si/SiO₂ substrate, indicating the amorphous structure of rubrene layer.